

# CPW2-1200S050–silicon Carbide Schottky Diode Chip

## ZERO RECOVERY<sup>®</sup> RECTIFIER

$V_{RRM}$	= 1200 V
$I_{F(AVG)}$	= 50 A
$Q_c$	= 305 nC

### Features

- 1200-Volt Schottky Rectifier
- Zero Reverse Recovery
- Zero Forward Recovery
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on  $V_F$

### Chip Outline



Part Number	Anode	Cathode	Package	Marking
CPW2-1200S050B	Al	NiV/Ag	Sawn on Foil	Wafer # on Foil

### Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V		
$V_{RSM}$	Surge Peak Reverse Voltage	1200	V		
$V_{DC}$	DC Blocking Voltage	1200	V		
$I_{F(AVG)}$	Average Forward Current	50	A	$T_J = 175^\circ\text{C}$	
$I_{FRM}$	Repetitive Peak Forward Surge Current	TBD	A	$T_C = 25^\circ\text{C}$ , $t_p = 8.3$ ms, Half Sine Wave	1
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	TBD	A	$T_C = 25^\circ\text{C}$ , $t_p = 10$ $\mu\text{s}$ , Pulse	1
$T_J, T_{stg}$	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		



## Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_F$	Forward Voltage	1.65 2.6	2.0 3.0	V	$I_F = 50\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 50\text{ A}$ $T_J = 175^\circ\text{C}$	
$I_R$	Reverse Current	10 50	200 1000	$\mu\text{A}$	$V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$	
$Q_C$	Total Capacitive Charge	305		nC	$V_R = 500\text{ V}$ , $I_F = 50\text{ A}$ $di/dt = 500\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	4500 396 325		pF	$V_R = 0\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$ $V_R = 200\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$ $V_R = 400\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$	

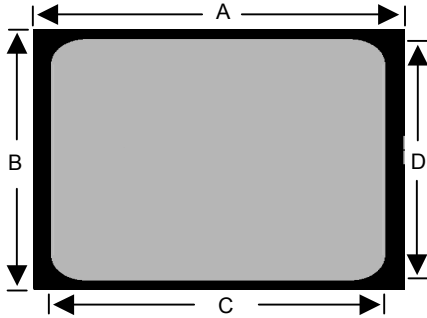
Note:

- Assumes  $\theta_{J-C}$  Thermal Resistance of  $0.5^\circ\text{C}/\text{W}$  or less.

## Mechanical Parameters

Parameter	Typ.	Unit
Die Size	4.02 x 8.23	mm
Anode Pad Size	3.58 x 7.77	mm
Anode Pad Opening	3.22 x 7.41	mm
Thickness	387 $\pm$ 10%	$\mu\text{m}$
Wafer Size	100	mm
Anode Metalization (Al)	4	$\mu\text{m}$
Cathode Metalization (Ni/Ag)	1.8	$\mu\text{m}$
Frontside Passivation	Nitride	

## Chip Dimensions



Symbol	Dimension	
	mm	inch
A	8.23	0.324
B	4.02	0.158
C	7.41	0.292
D	3.22	0.127

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CPW2-1200S050B	Al	NiV/Ag	Sawn on Foil	Wafer # on Foil

The die-on-tape method of delivering these SiC die may be considered a means of temporary storage only. Due to an increase in adhesion over time, die stored for an extended period may affix too strongly to the tape. These die should be stored in a temperature-controlled, nitrogen dry box soon after receipt. Cree will further recommend that all die be removed from tape to a wafer pack, to a similar storage medium, or used in production within 2 - 3 weeks of delivery to assure 100% release of all die without issues.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, air traffic control systems, or weapons systems.

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